

General Description

The 180P04 is a P-channel Power MOSFET. They use advanced trench technology to provide excellent $R_{DS(ON)}$. The device is therefore suitable in advanced high-efficiency switching applications.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
-40V	5mΩ	-100A

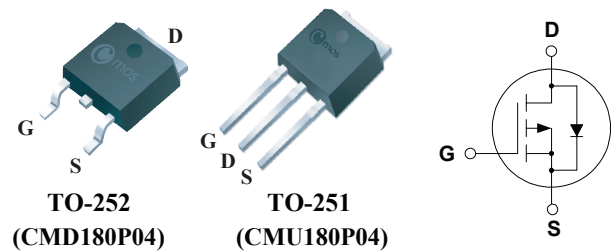
Applications

- DC-DC Converters
- Motor control

Features

- P-Channel MOSFET
- Low ON-resistance
- 100% avalanche tested
- RoHS Compliant

TO-252/251 Pin Configuration



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	-100	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	-70	A
I_{DM}	Pulsed Drain Current	-400	A
EAS	Single Pulse Avalanche Energy ¹	1058	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	136	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.92	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-20A$	---	4	5	mΩ
		$V_{GS}=-4.5V$, $I_D=-20A$	---	4.8	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D = -250\mu A$	-1.0	---	-3.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-40V$, $V_{GS}=0V$	---	---	-1	uA
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V$, $I_D=-20A$	---	46	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	9	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-32V$, $V_{GS}=-10V$, $I_D=-80A$	---	200	---	nC
Q_{gs}	Gate-Source Charge		---	25	---	
Q_{gd}	Gate-Drain Charge		---	53	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-20V$, $V_{GS} = -10V$, $R_G=0\Omega$ $I_D=-40A$	---	35	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	245	---	
T_f	Fall Time		---	120	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1MHz$	---	11500	---	pF
C_{oss}	Output Capacitance		---	750	---	
C_{rss}	Reverse Transfer Capacitance		---	515	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-100	A
I_{SM}	Pulsed Source Current		---	---	-400	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=-20A$, $T_J=25^{\circ}\text{C}$	---	-0.79	-1.3	V

Note :

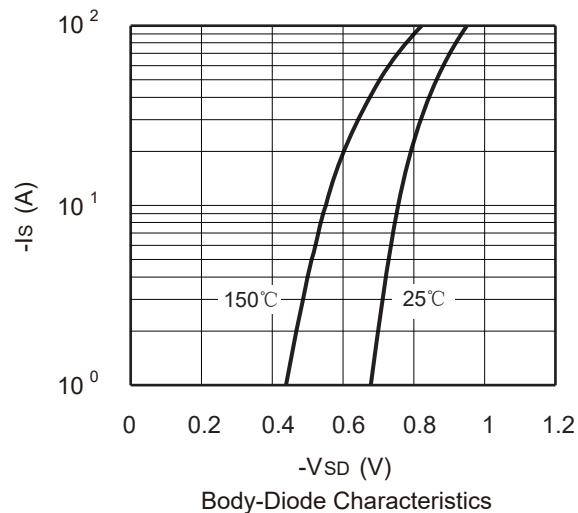
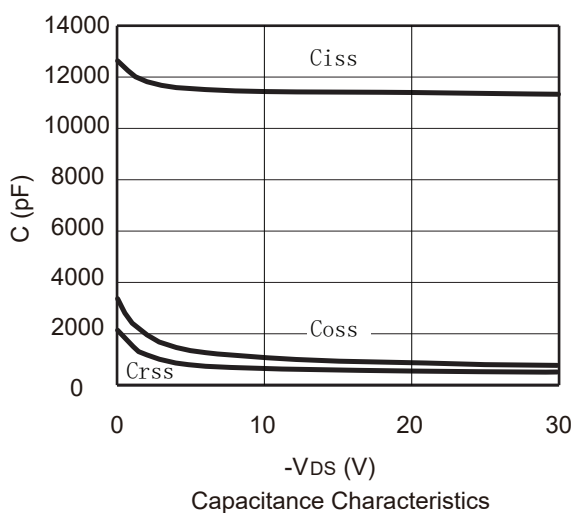
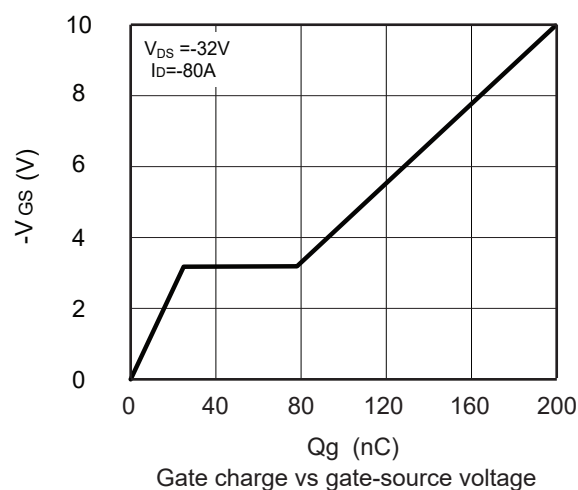
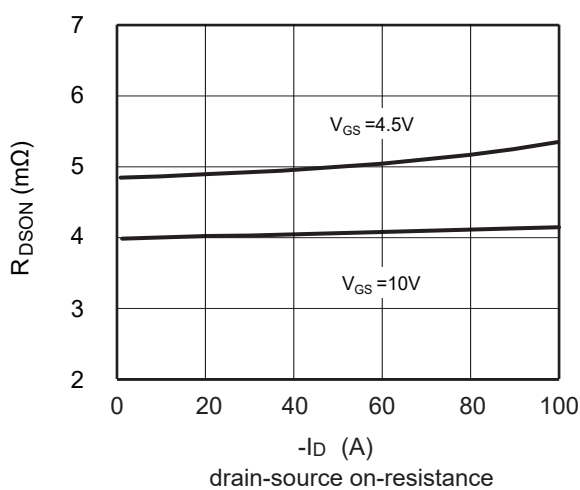
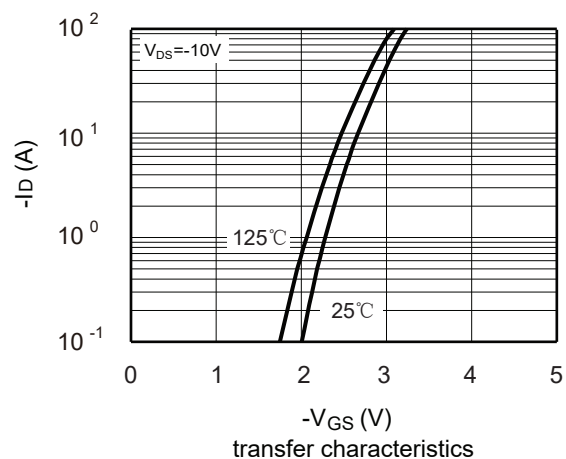
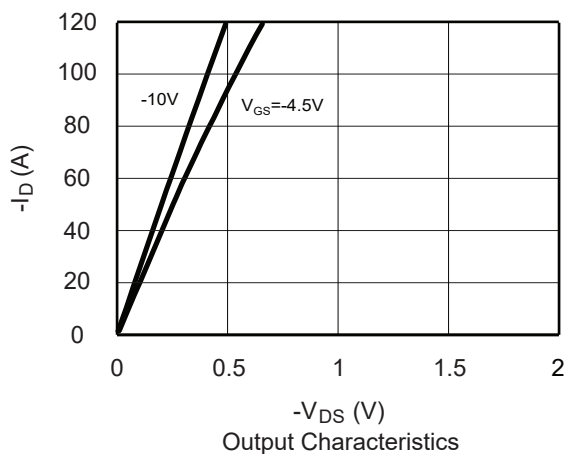
1.The EAS data shows Max. rating . The test condition is $V_{DD}=-35V$, $V_{GS}=-10V$, $L=1mH$, $I_{AS}=-46A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design , functions and reliability without notice. Please refer to the latest version of specification.

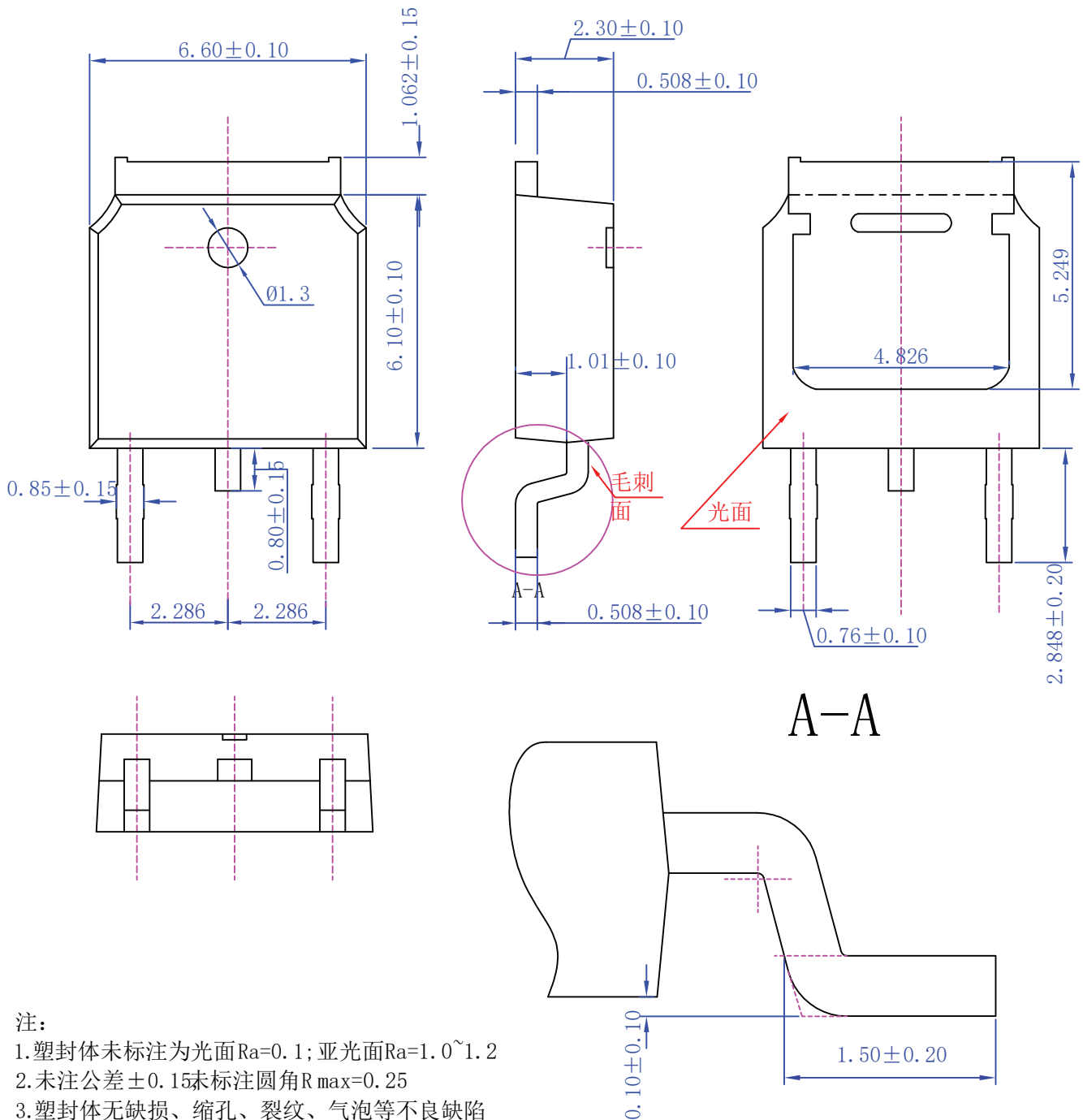
Typical Characteristics



Package Dimension

TO-252

Unit :mm



注:

1. 塑封体未标注为光面 $Ra=0.1$; 亚光面 $Ra=1.0 \sim 1.2$
2. 未注公差 ± 0.15 未标注圆角 $R_{max}=0.25$
3. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
4. 标注单位mm
5. 顶针孔不允许凸出塑封体表面

Unit :mm

